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(54) **SEMICONDUCTOR DEVICE AND THE
MANUFACTURING METHOD THEREOF**

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ABSTRACT

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A semiconductor device includes a substrate, a plurality of epitaxial structures and a plurality of gate structures. The substrate includes a plurality of recesses and a plurality of convex portions. Each of the convex portions is located between the two adjacent recesses, in which each of a sidewall of the recesses includes at least two concave portions. Each of the concave portions includes a first inclined plane and an adjacent second inclined plane. The second inclined plane of one of the concave portions is adjacent to a first inclined plane of another one of the concave portions, such that the sidewall has a zig-zag shape. The epitaxial structures are located in the recesses of the substrate respectively. The gate structures are located on the convex portions of the substrate respectively.

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